Session Title: 19. Oxide Materials for Backplane

Date: Aug. 30, 2017 (Wednesday)

Time: 09:00-10:30

Room C (Room 101-102)

Session Chairs
Prof. Toshio Kamiya (Tokyo Inst. of Tech., Japan)
Prof. Fukai Shan (Qingdao Univ., China)

[C19-1] 09:00-09:25

[Invited] Excellent Optical Performance and Reliability Improvement on a IGZO-Driven Flexible LCD

Yen-Yu Huang (Chunghwa Picture Tubes, Taiwan)

[C19-2] 09:25-09:50

[Invited] Highly Reliable Top Gate Oxide TFT for AMOLED Applications

Chen-Shuo Huang, Yang-shun Fan, Ling-Ying Lin, Yun-Rong Yang, Ching-Hao Wang, Shang-Lin Wu, Guan-Yu Lin, Kuo-Kuang Chen, Ya-Ling Chen, Kuo-Che Tseng, Chien-Ya Lee, Wei-Yuan Wang, Che-Ming Hsu, Ya-Fei Kuo, Hsueh-Hsing Lu, and Yu-Hsin Lin (AU Optronics Corp)

[C19-3] 09:50-10:15

[Invited] Organic Thin-Film Transistors with Mobility Over 10 cm²/Vs by Low-Temperature Solution Coating

Chuan Liu (Sun Yat-sen Univ., China), Xuying Liu, Takeo Minari (NIMS, Japan), Masayuki Kanehara (C-ink. Co., Ltd., Japan), and Yong-Young Noh (Dongguk Univ., Korea)

[C19-4] 10:15-10:30

A 31-in UD AM-OLED Display Using Self-Aligned Top Gate IGZO TFTs

Yanhong Meng, Shan Li, Shimin Ge, Xiangyong Kong, Chunsheng Jiang, Wen Shi, Wei Wu, Feng Zhu, Xiang Liu, and Chia Yu Lee (Shenzhen China Star Optoelectronics Tech. Co., Ltd., China)